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PSMN4R8-100BSE

N-channel 100 V 4.8 mΩ standard level MOSFET in D2PAK

12 April 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. Part of NXP's "NextPower Live" portfolio, the PSMN4R8-100BSE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn on, whilst offering a low $R_{DS(on)}$ characteristic to keep temperatures down and efficiency up in continued use. Ideal for telecommunication systems based on a 48 V backplane / supply rail.

2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low $R_{DS(on)}$ for low conduction losses

3. Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	100	V
I_{DM}	peak drain current	pulsed; $T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	-	707	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2	-	-	405	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12	-	4.1	4.8	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; Fig. 14 ; Fig. 15	-	59	83	nC
$Q_{G(tot)}$	total gate charge		-	196	278	nC



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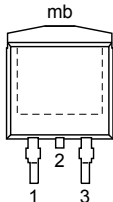
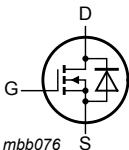
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 120\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3	-	-	542	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>D2PAK (SOT404)</p>	 <p>mbb076</p>
2	D	drain ^[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R8-100BSE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R8-100BSE	PSMN4R8-100BSE

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V

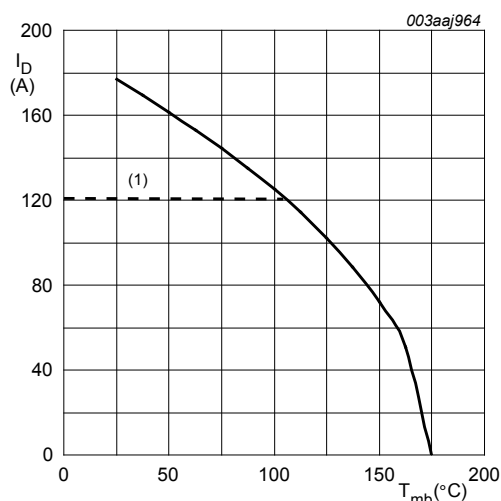
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Symbol	Parameter	Conditions		Min	Max	Unit
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_j = 25\text{ °C}$; Fig. 1	[1]	-	120	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 1	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 4		-	707	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	405	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	707	A
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 120\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3		-	542	mJ

[1] Continuous current limited by package.



(1) Capped at 120A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10\text{ V}$$

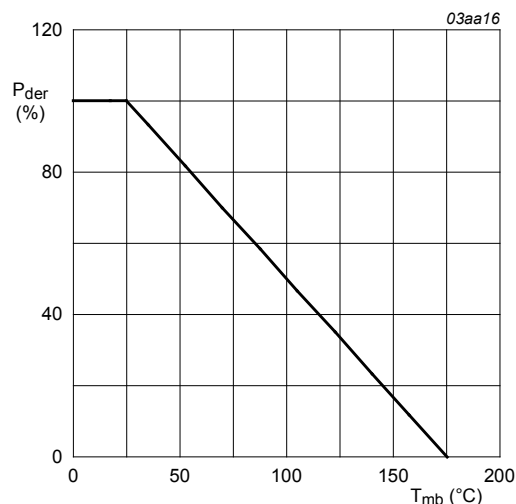


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

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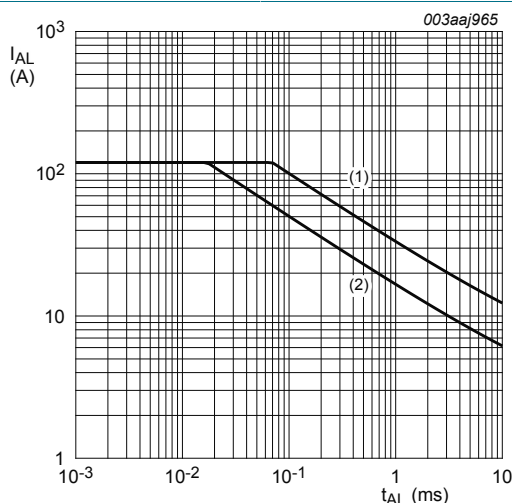


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j \text{ (initial)}} = 25^{\circ}\text{C}$; (2) $T_{j \text{ (initial)}} = 100^{\circ}\text{C}$

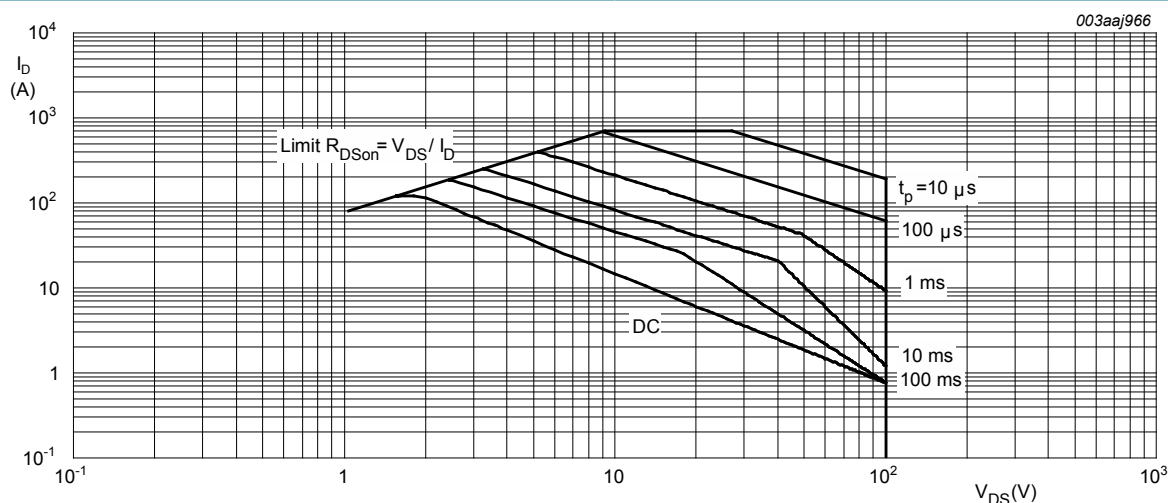


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse; Capped at 120 A due to package

9. Thermal characteristics

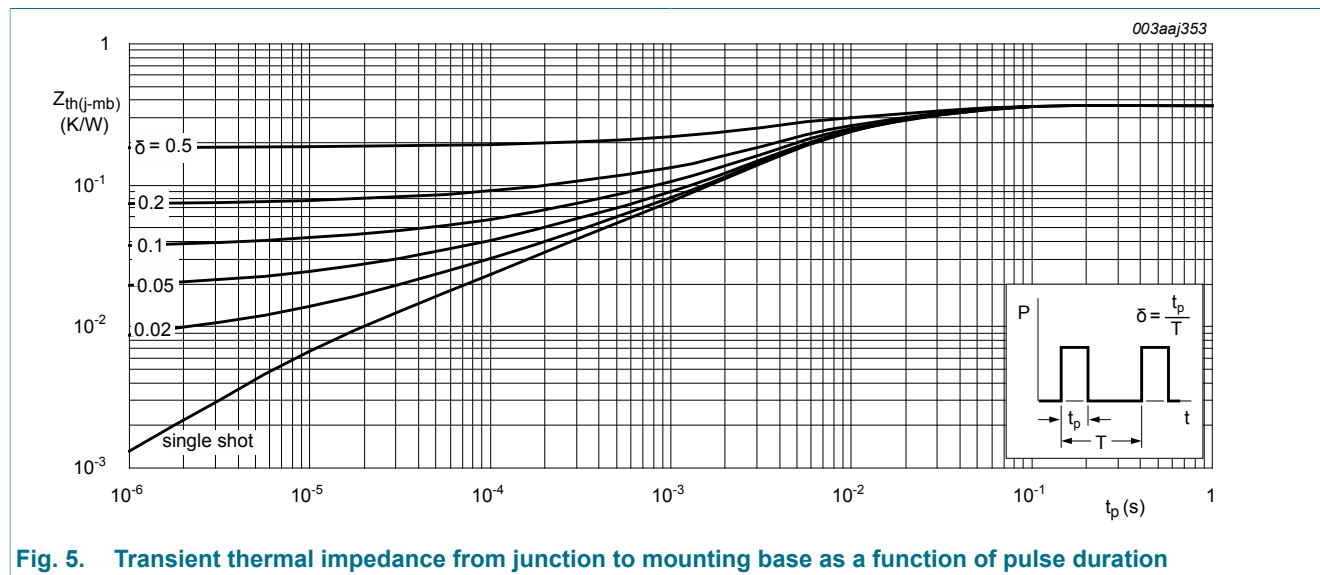
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.3	0.37	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 ^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 ^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS} = V_{GS}; T_J = 25 ^\circ C$; Fig. 10 ; Fig. 11	2	3	4	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS} = V_{GS}; T_J = 175 ^\circ C$; Fig. 11	1	-	-	V
		$I_D = 1 mA; V_{DS} = V_{GS}; T_J = -55 ^\circ C$; Fig. 11	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 V; V_{GS} = 0 V; T_J = 25 ^\circ C$	-	0.16	10	μA
		$V_{DS} = 100 V; V_{GS} = 0 V; T_J = 175 ^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 V; V_{DS} = 0 V; T_J = 25 ^\circ C$	-	10	100	nA
		$V_{GS} = 20 V; V_{DS} = 0 V; T_J = 25 ^\circ C$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_J = 25 ^\circ C$; Fig. 12	-	4.1	4.8	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_J = 100 ^\circ C$; Fig. 13 ; Fig. 12	-	-	8.7	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_J = 175 ^\circ C$; Fig. 12 ; Fig. 13	-	-	13	mΩ
R_G	gate resistance	$f = 1 MHz$	0.43	0.85	1.7	Ω

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15		-	196	278	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V		-	166.9	234	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15		-	40	56	nC
Q _{GD}	gate-drain charge			-	59	83	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 50 V; Fig. 14 ; Fig. 15		-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16		-	10665	14400	pF
C _{oss}	output capacitance			-	674	910	pF
C _{rss}	reverse transfer capacitance			-	459	643	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; R _L = 2 Ω; V _{GS} = 10 V; R _{G(ext)} = 4.7 Ω		-	41	61.5	ns
t _r	rise time			-	65	97.5	ns
t _{d(off)}	turn-off delay time			-	127	190.5	ns
t _f	fall time			-	69	103.5	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 17		-	0.79	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 50 V		-	72	94	ns
Q _r	recovered charge			-	227	296	nC

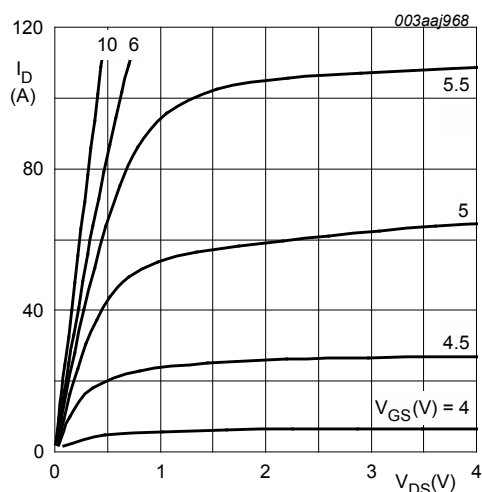


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

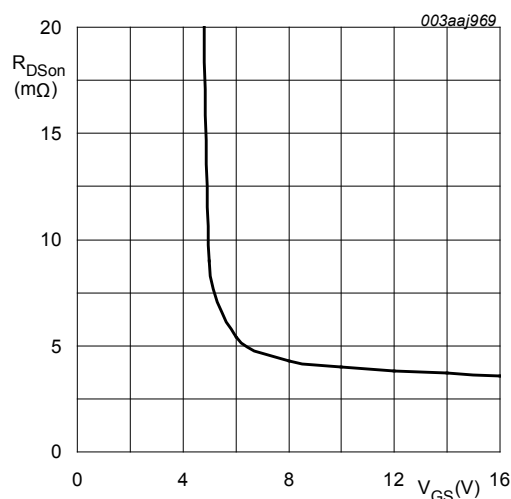


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}$; $I_D = 25\text{ A}$

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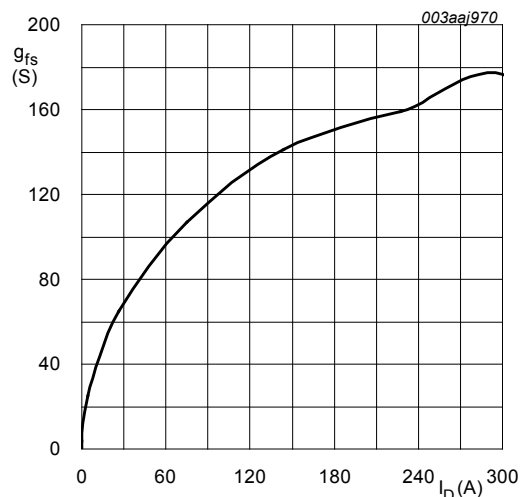


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$$

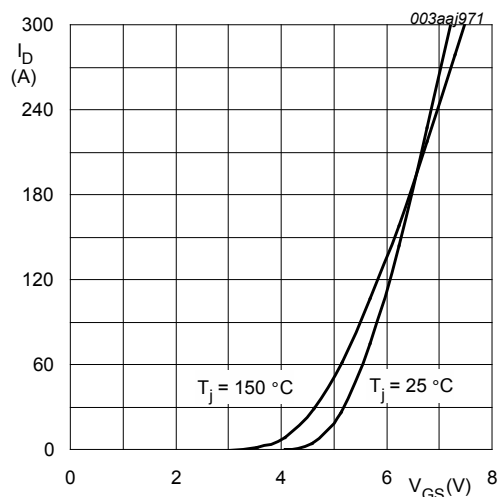


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10\text{V}$$

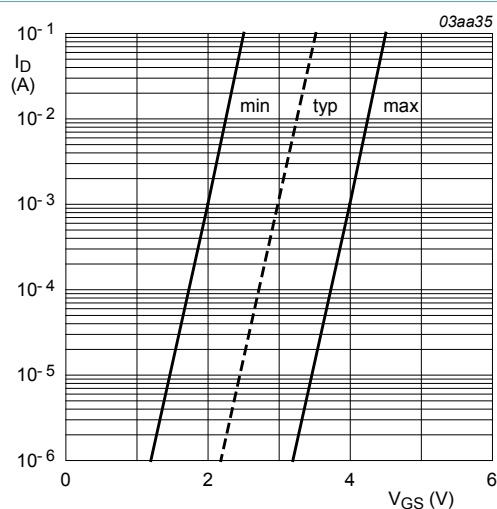


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

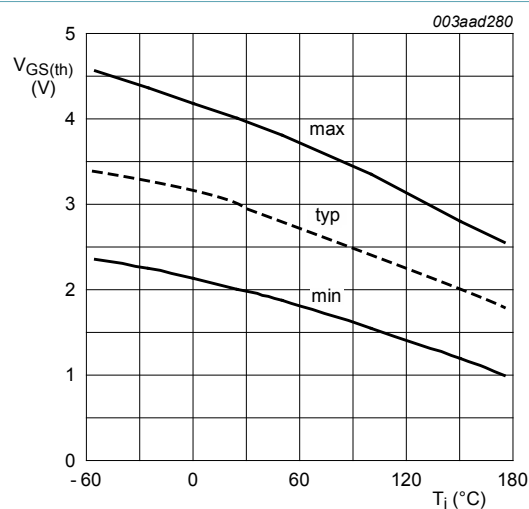


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

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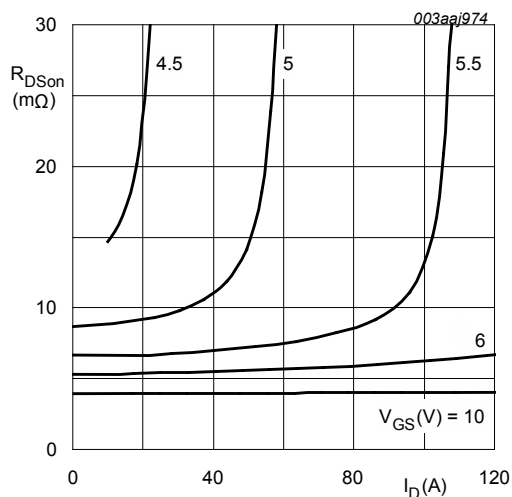


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

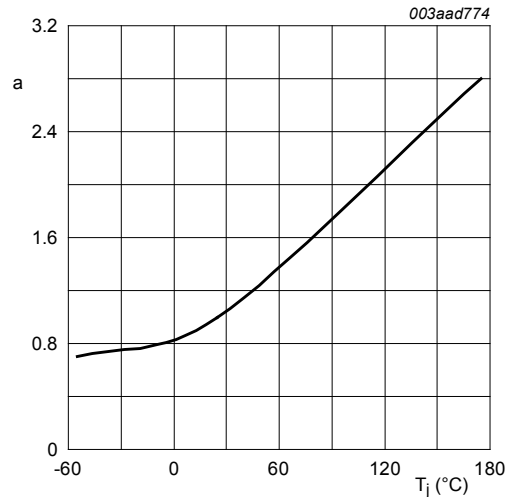


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)25^\circ\text{C}}}$$

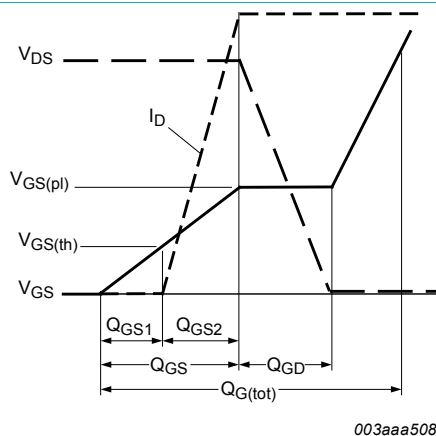


Fig. 14. Gate charge waveform definitions

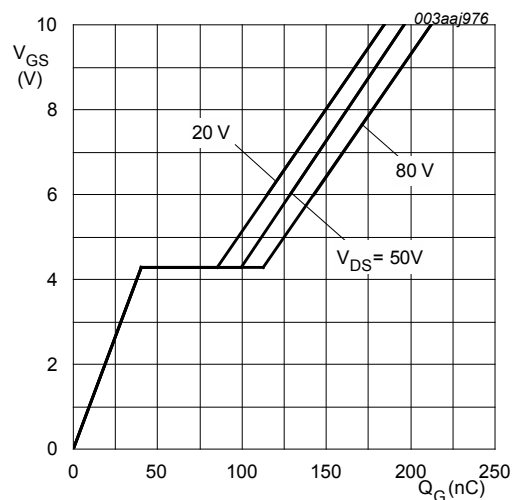


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

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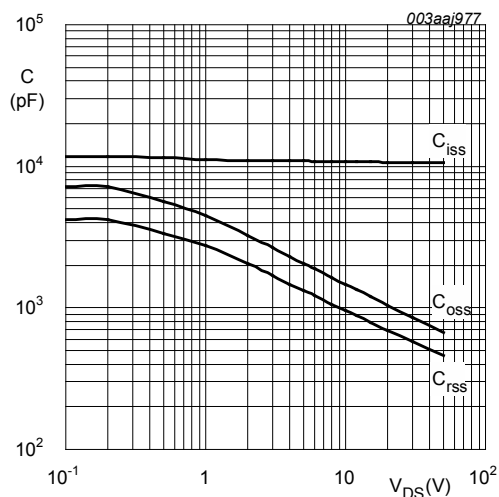


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

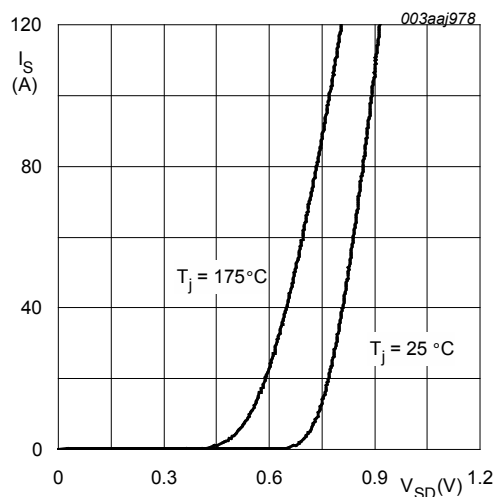


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

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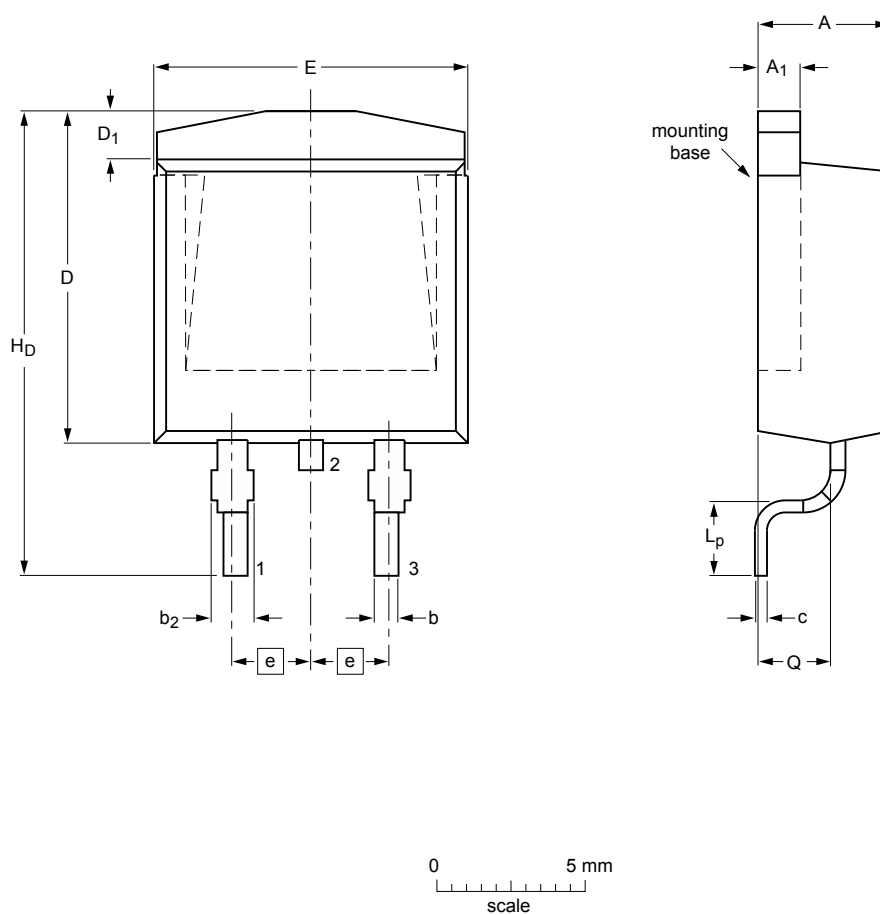
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11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₂	c	D	D ₁	E	e	H _D	L _p	Q
max	4.5	1.40	0.85	1.45	0.64	11	1.6	10.3	2.54	15.8	2.9	2.6
nom												
min	4.1	1.27	0.60	1.05	0.46		1.2	9.7		14.8	2.1	2.2

sot404_po


Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT404						-06-03-16- 13-02-25

Fig. 18. Package outline D2PAK (SOT404)

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12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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